



DESCRIPTION:

The JST08H-600BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST08H-600BW snubberless triac is especially recommended for use on inductive loads. From T2 terminals to external heatsink. Package TO-251 is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	600	V
$I_{GT} / /$	50/50/50	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	600	V
RMS on-state current ($T_c = 91^\circ C$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle, $t_p=20ms$, $T_j=25^\circ C$)	I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$, $T_j=25^\circ C$)		88	
I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$)	I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^\circ C$)	di/dt	100	A/s
Peak gate current ($t_p=20 \mu s$, $T_j=125^\circ C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	2.5	kV
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ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				90	
I_H	$I_T=100mA$		MAX.	50	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125$		MIN.	2000	V s
$(dI/dt)_c$	$(dV/dt)_c=20V/s, T_j=125$		MIN.	12	A/ms
t_{on}	$I_G=80mA I_A=400mA I_R=40mA$ $T_j=25$		TYP.	5	s
t_{off}				50	

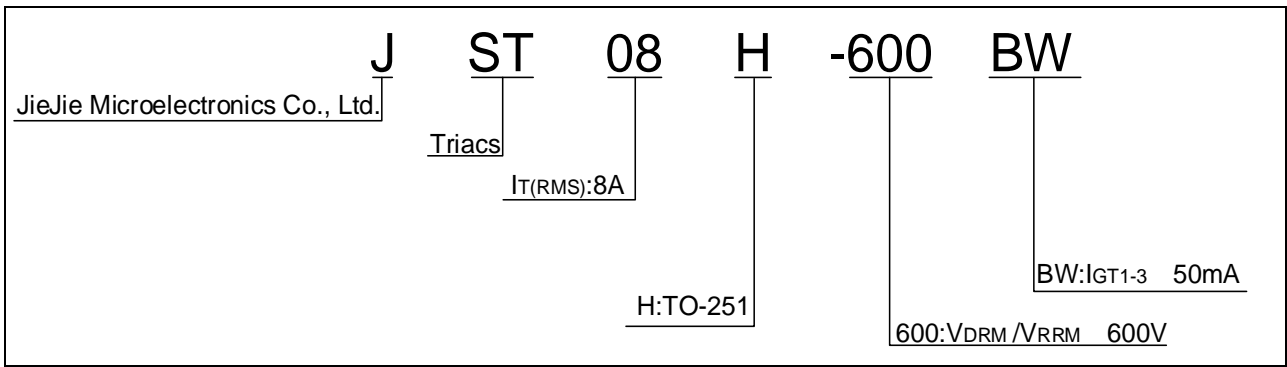
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=11A t_p=380 \mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.8	V
R_D	Dynamic resistance	$T_j=125$	44	P
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	A
I_{RRM}		$T_j=125$	0.25	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	3	$^{\circ}W$
$R_{th(j-a)}$	junction to ambient (AC)	100	$^{\circ}W$

ORDERING INFORMATION



MARKING

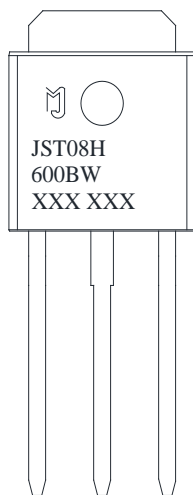


FIG.1: Maximum power dissipation versus RMS on-state current

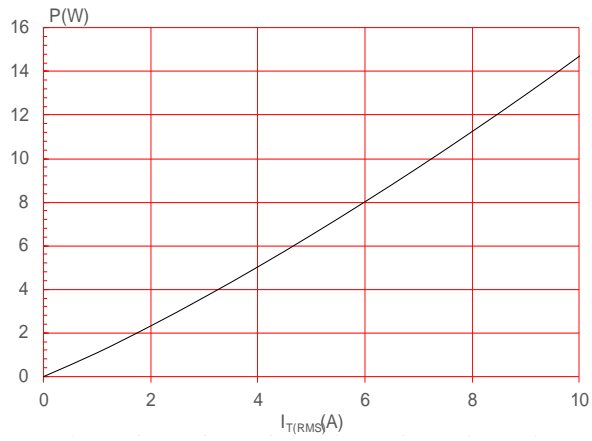


FIG.2: RMS on-state current versus case temperature

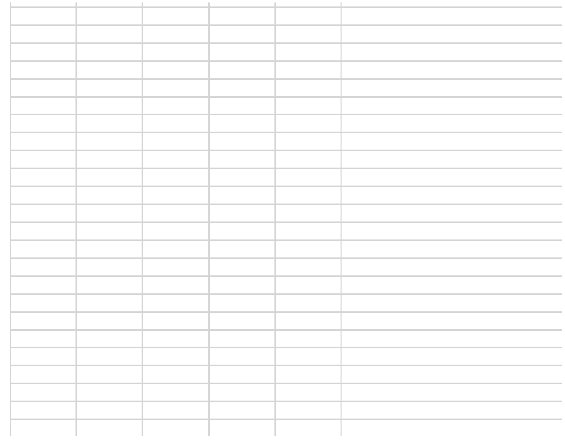
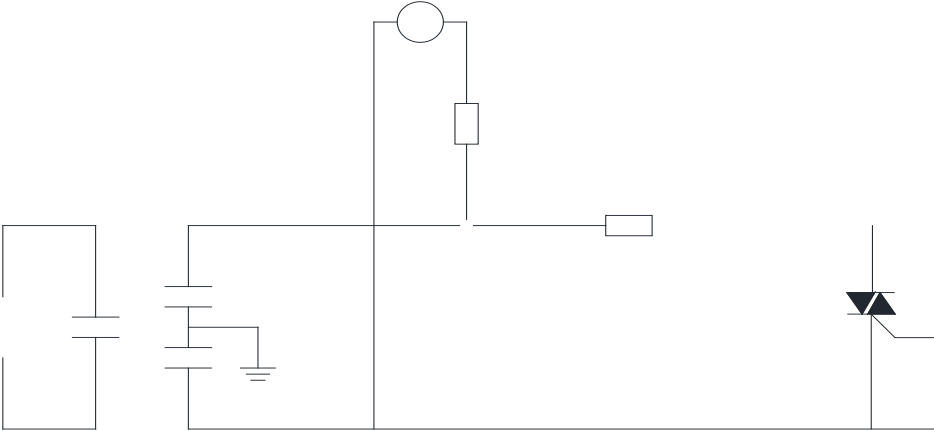


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



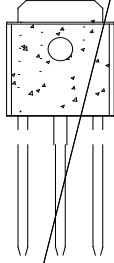
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST08H-600BW	600	50	TO-251	80	Tube

Document Revision History

Date	Revision
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PACKAGE MECHANICAL DATA



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